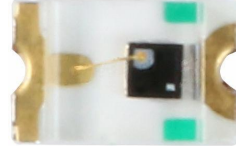


## Technical Data Sheet

### 0805 SMD Phototransistor: PT0805CS

#### ■ Features

- . Fast response time
- . High photo sensitivity
- . Pb free
- . Compliance with EU REACH
- . The product itself will remain within RoHS compliant version.



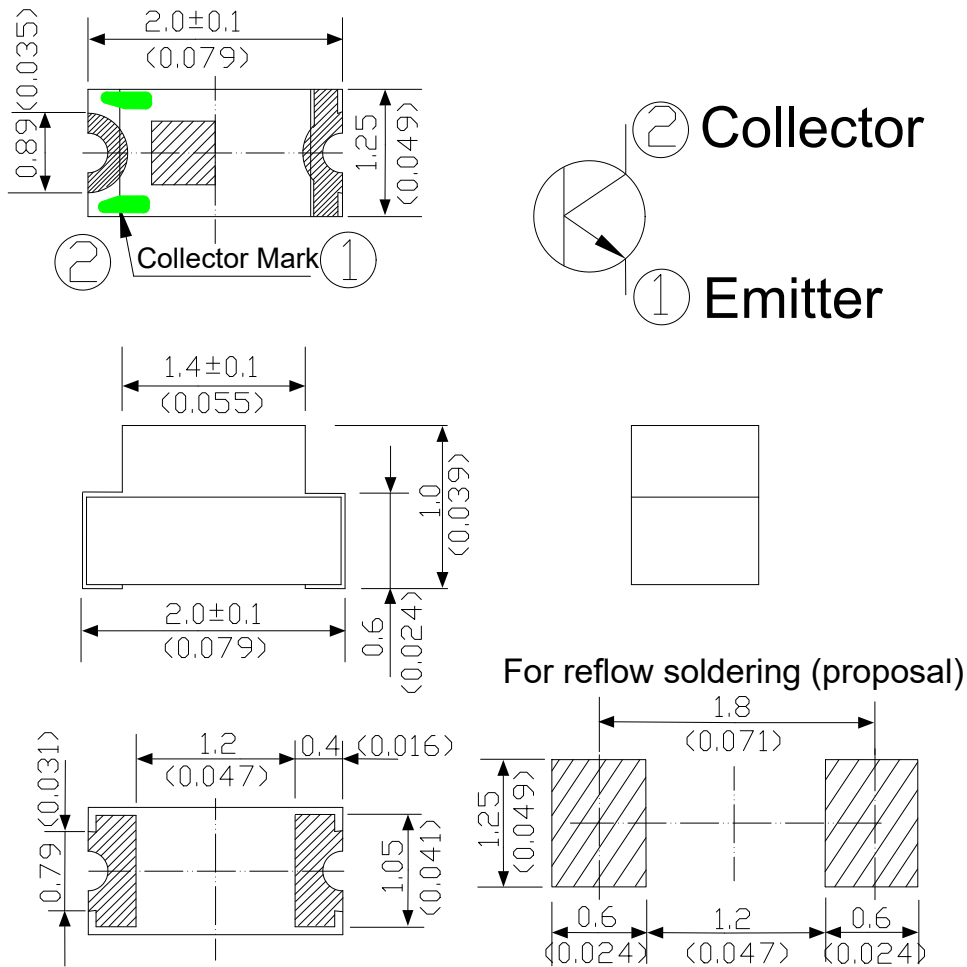
#### ■ Descriptions

PT0805CS is a high speed and high sensitive NPN silicon planar phototransistor in a miniature flat top view lens SMD package. The device is spectrally matched to visible and infrared emitting diode.

#### ■ Applications

- . Infrared applied system
- . Miniature switch
- . Position sensor
- . Encoder
- . Counters and sorter

## ■ Package Dimensions



- Note: 1. All dimensions are in millimeters(inches)  
 2. Tolerances unless dimensions  $\pm 0.1\text{mm}(.004\text{'})$   
 3. Suggested pad dimension is just for reference only  
 Please modify the pad dimension based on need

## ■ Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Collector-Voltage	$V_{ECO}$	5	V
Collector Current	$I_C$	20	mA
Power Dissipation at (or below) 25°C Free Air Temperature	$P_c$	75	mW
Lead Soldering Temperature	$T_{sol}$	260	$^\circ\text{C}$
Operating Temperature	$T_{opr}$	-20 ~ +85	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 ~ +85	$^\circ\text{C}$

### ■ Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Range of Spectral Bandwidth	$\lambda_{0.5}$	---	400	--	1100	nm
Wavelength of Peak Sensitivity	$\lambda_p$	---	--	940	--	nm
Collector – Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=100\mu A$ $E_e=0mW/cm^2$	30	--	--	V
Emitter-Collector Breakdown Voltage	$BV_{ECO}$	$I_E=100\mu A$ $E_e=0mW/cm^2$	5	--	--	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	--	--	0.4	V
Rise Time	$t_r$	$V_{CE}=5V$ $I_C=1mA$	--	15	--	$\mu S$
Fall Time	$t_f$	$RL=1000\Omega$	--	15	--	$\mu S$
DC Current Amplification Factor	$H_{FE}$	$V_{CE}=5V$ , $I_C=2mA$	1000	--	1800	
Collector Dark Current	$I_{CEO}$	$E_e=0mW/cm^2$ $V_{CE}=20V$	--	--	100	nA
On State Collector Current	$I_{C(on)}$	$E_e=1mW/cm^2$ $V_{CE}=5V$	0.3	1.0	--	mA

### ■ Typical Electro-Optical Characteristics Curves

Fig.1 Collector Power Dissipation vs. Ambient Temperature

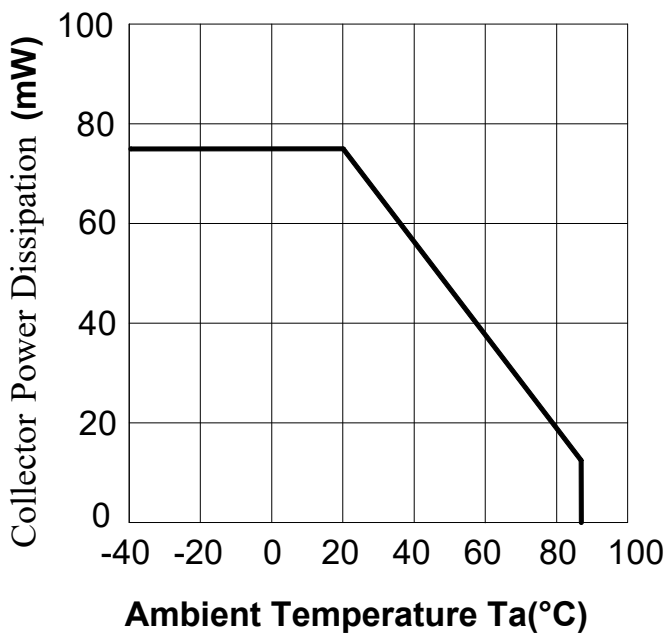


Fig.2 Spectral Sensitivity

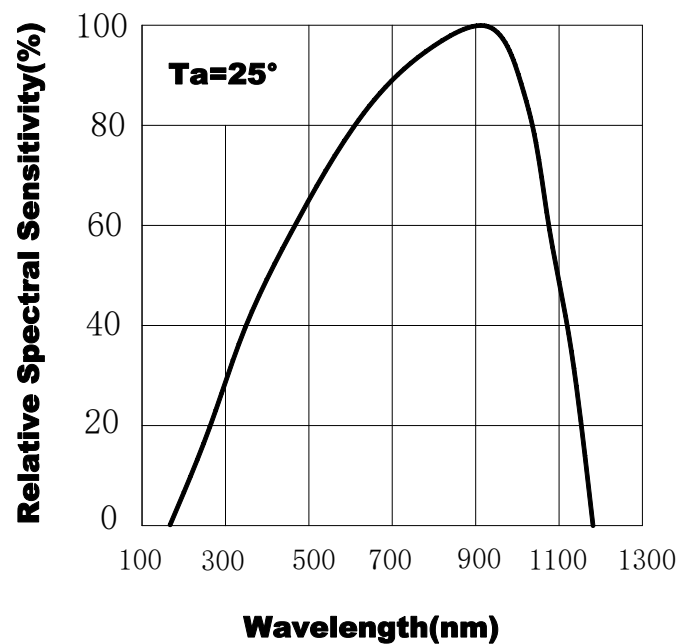


Fig.3 Relativ Collector Current vs. Ambient Temperature

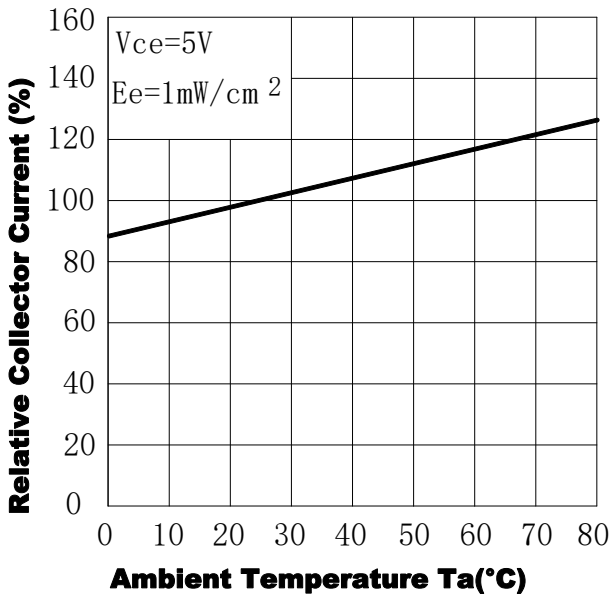


Fig.4 Collector Current vs. Irradiance

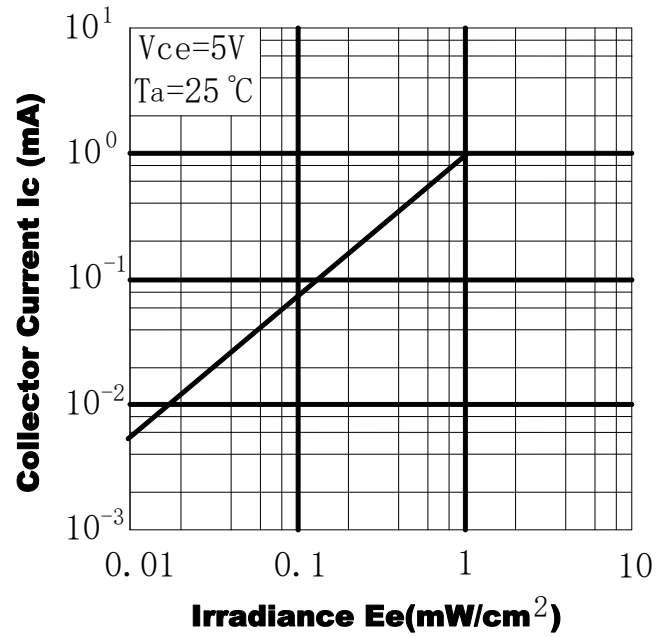


Fig.5 Collector Dark Current vs. Ambient Temperature

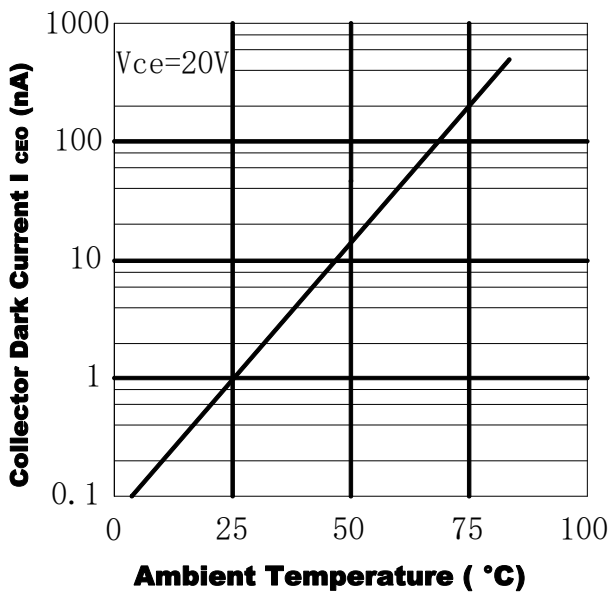
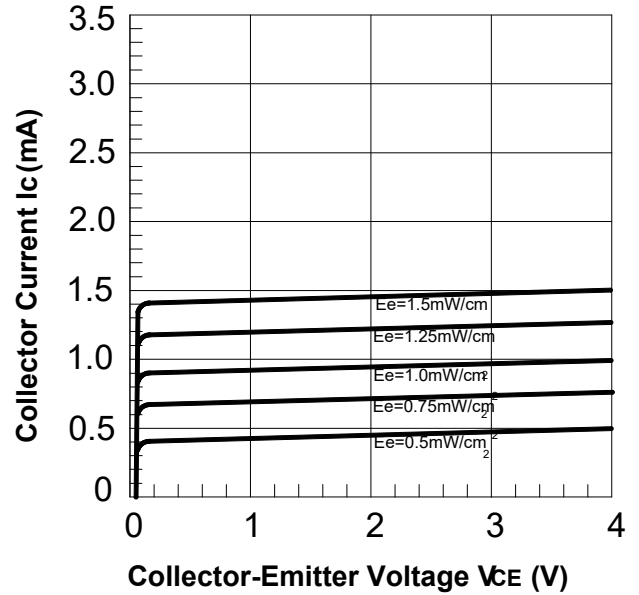
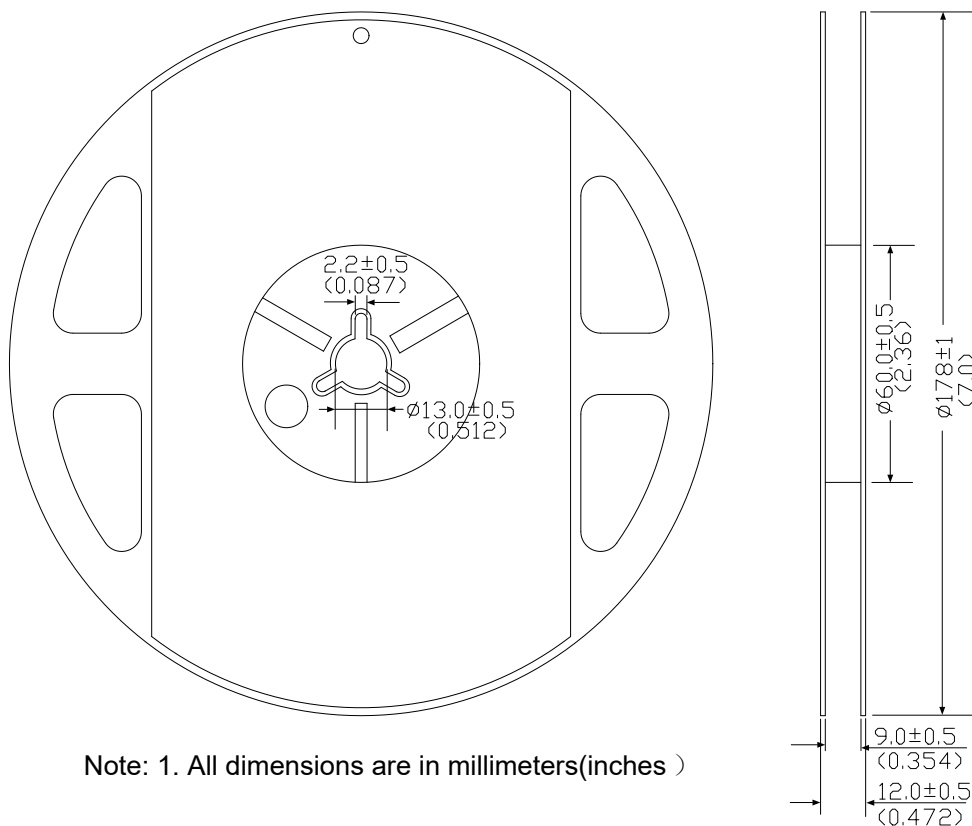


Fig.6 Collector Current vs. Collector-Emitter Voltage

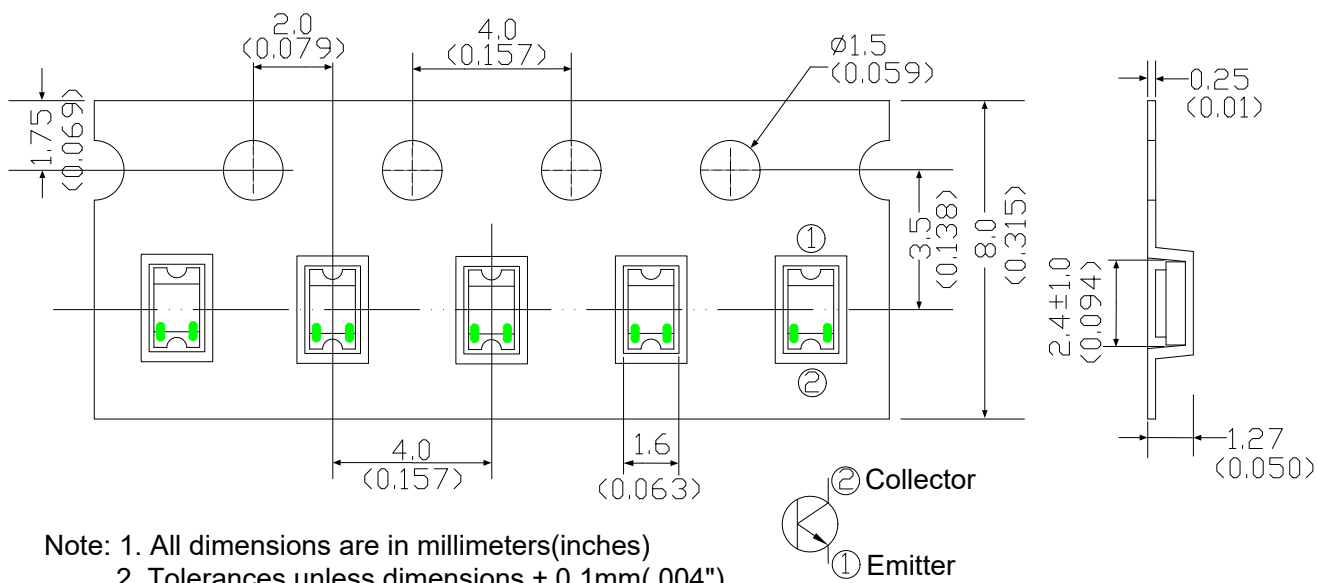


■ Packing Dimensions



Note: 1. All dimensions are in millimeters(inches )

■ Carrier Tape Dimensions (Quantity: 3000 pcs/reel)



Note: 1. All dimensions are in millimeters(inches)  
 2. Tolerances unless dimensions  $\pm 0.1\text{mm}(.004\text{'})$

■ **Notes**

1. Above specification may be changed without notice. SHUGUAN will reserve authority on material change for above specification.
2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. SHUGUAN assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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